

International IR Rectifier

PD - 95456

IRLIZ44NPbF

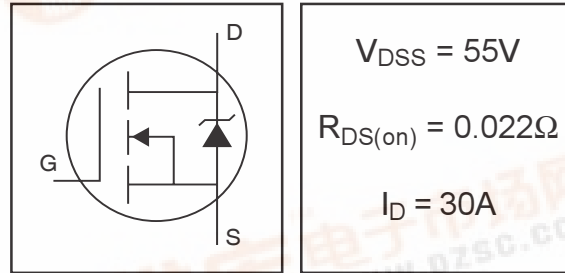
HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

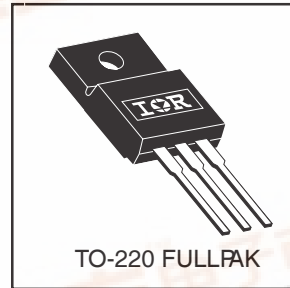
Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



$V_{DSS} = 55V$
$R_{DS(on)} = 0.022\Omega$
$I_D = 30A$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	30	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	22	
I_{DM}	Pulsed Drain Current ①⑥	160	
$P_D @ T_C = 25^\circ C$	Power Dissipation	45	W
	Linear Derating Factor	0.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy②⑥	210	mJ
I_{AR}	Avalanche Current③⑥	25	A
E_{AR}	Repetitive Avalanche Energy①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑥	5.0	V/ns
T_J	Operating Junction and Storage Temperature Range	-55 to + 175	°C
T_{STG}			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

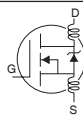
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	3.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient	---	65	

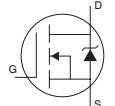
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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.070	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ Ⓞ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.022	Ω	$V_{GS} = 10V, I_D = 17A$ Ⓞ
		—	—	0.025		$V_{GS} = 5.0V, I_D = 17A$ Ⓞ
		—	—	0.035		$V_{GS} = 4.0V, I_D = 14A$ Ⓞ
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	21	—	—	S	$V_{DS} = 25V, I_D = 25A$ Ⓞ
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	48	nC	$I_D = 25A$
Q_{gs}	Gate-to-Source Charge	—	—	8.6		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	25		$V_{GS} = 5.0V$, See Fig. 6 and 13 ⓄⓅ
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	84	—		$I_D = 25A$
$t_{d(off)}$	Turn-Off Delay Time	—	26	—		$R_G = 3.4\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	15	—		$R_D = 1.1\Omega$, See Fig. 10 ⓄⓅ
L_D	Internal Drain Inductance	—	4.5	—		nH
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1700	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	400	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	150	—		$f = 1.0\text{MHz}$, See Fig. 5Ⓞ
C	Drain to Sink Capacitance	—	12	—		$f = 1.0\text{MHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	30	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ⓁⓄ	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 17A, V_{GS} = 0V$ Ⓞ
t_{rr}	Reverse Recovery Time	—	80	120	ns	$T_J = 25^\circ\text{C}, I_F = 25A$
Q_{rr}	Reverse Recovery Charge	—	210	320	μC	$di/dt = 100A/\mu s$ ⓄⓅ
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 15V$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu H$
 $R_G = 25\Omega, I_{AS} = 25A$. (See Figure 12)
- ③ $I_{SD} \leq 25A, di/dt \leq 270A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ $t = 60s, f = 60\text{Hz}$

⑥ Uses IRLZ44N data and test conditions

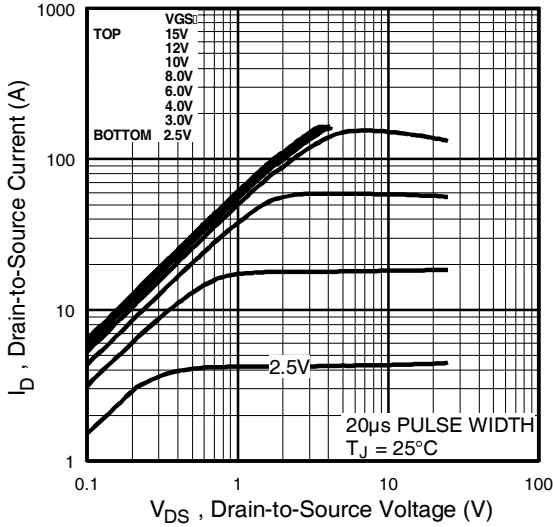


Fig 1. Typical Output Characteristics

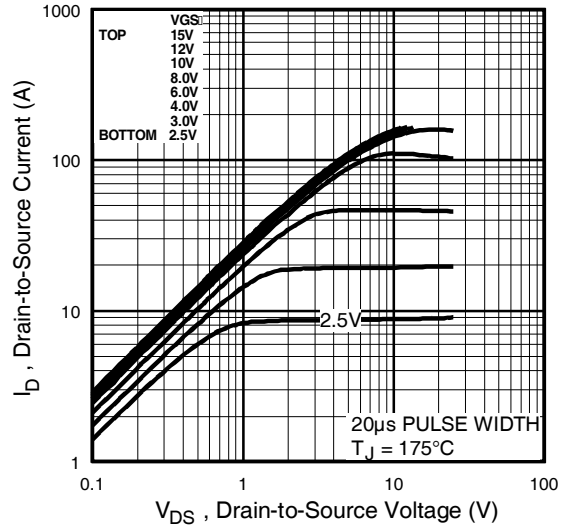


Fig 2. Typical Output Characteristics

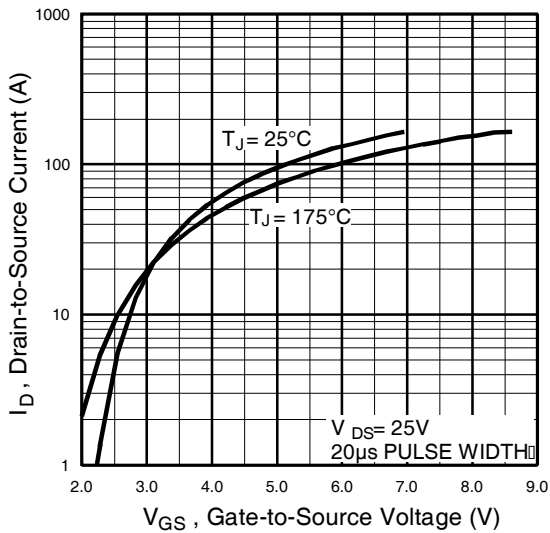


Fig 3. Typical Transfer Characteristics

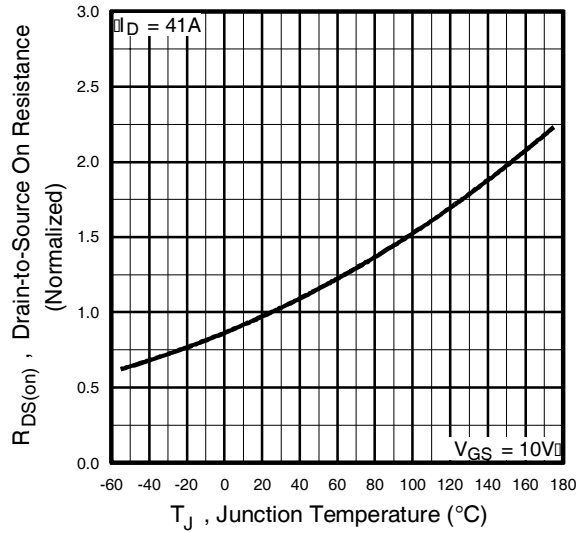


Fig 4. Normalized On-Resistance Vs. Temperature

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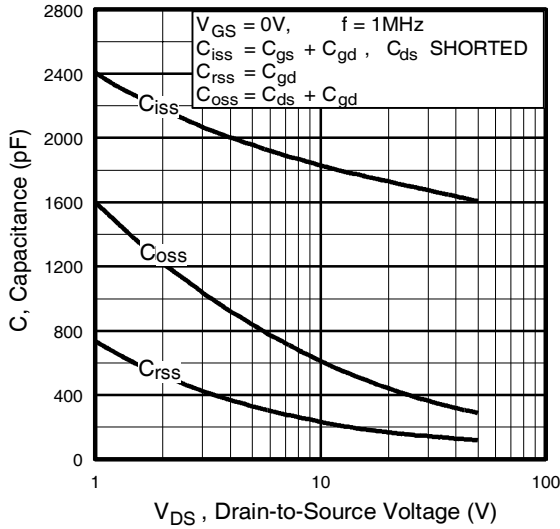


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

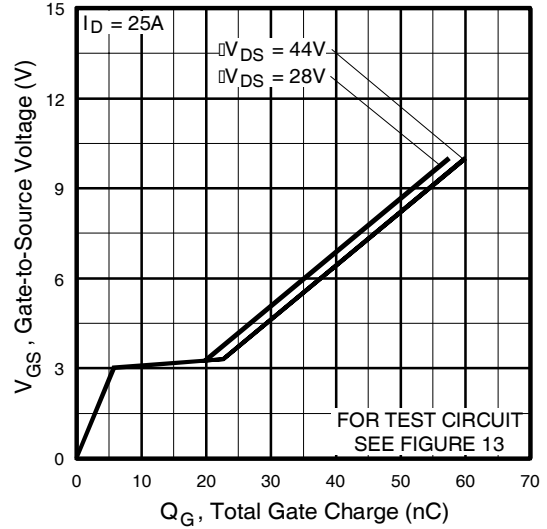


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

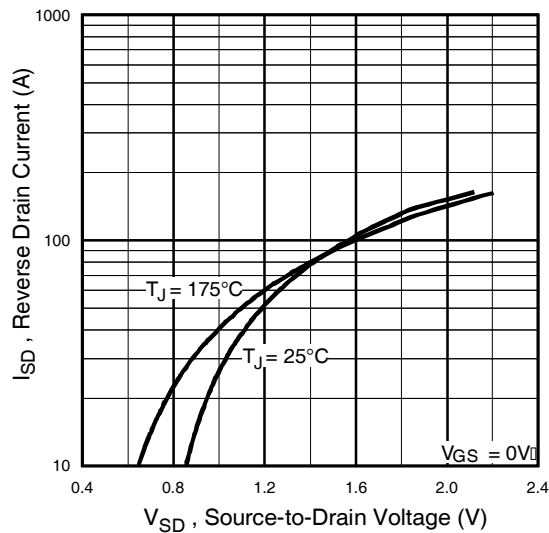


Fig 7. Typical Source-Drain Diode Forward Voltage

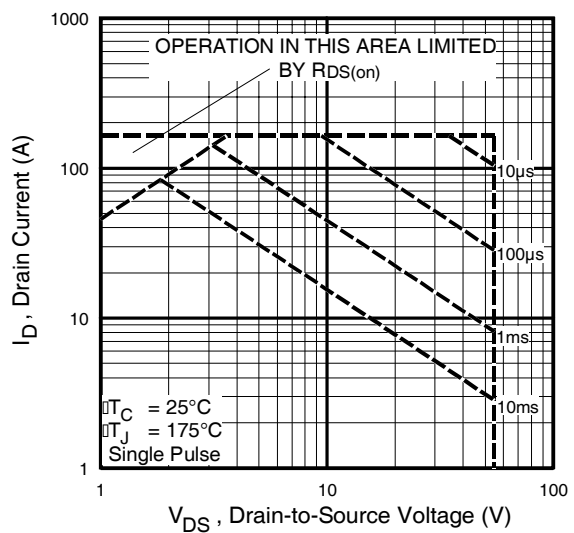


Fig 8. Maximum Safe Operating Area

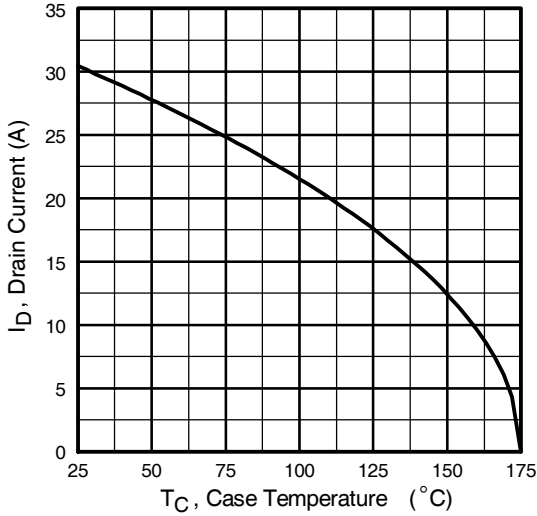


Fig 9. Maximum Drain Current Vs. Case Temperature

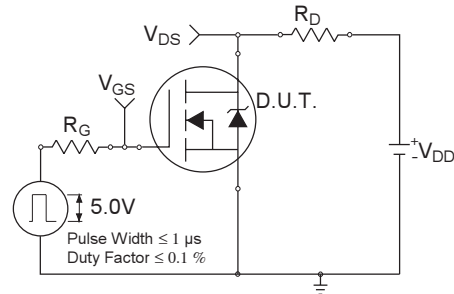


Fig 10a. Switching Time Test Circuit

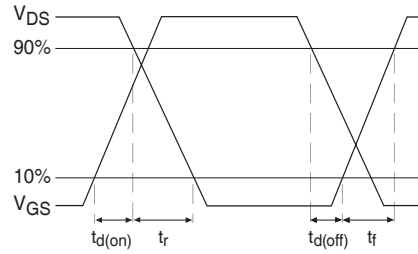


Fig 10b. Switching Time Waveforms

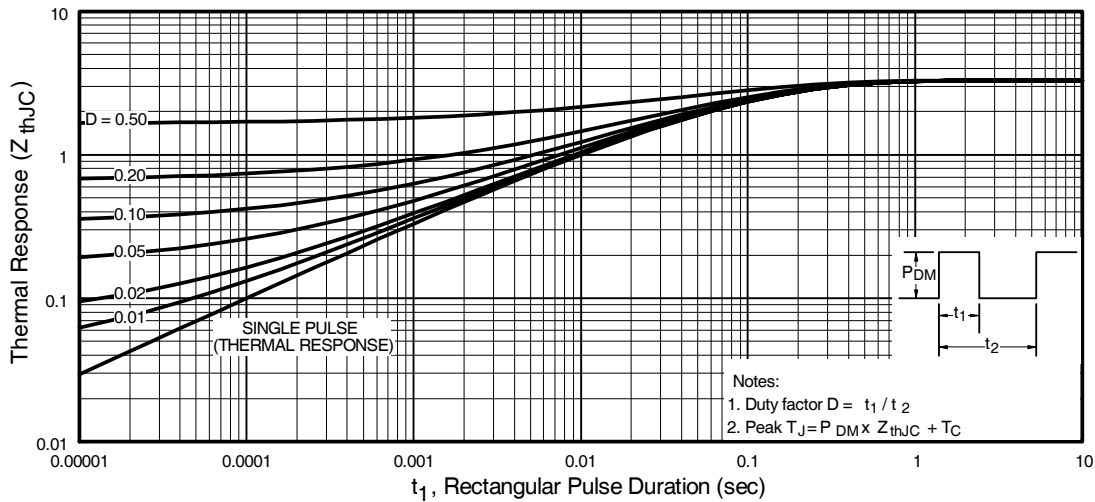


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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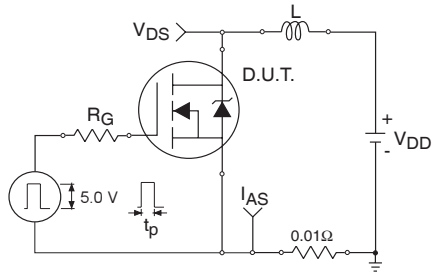


Fig 12a. Unclamped Inductive Test Circuit

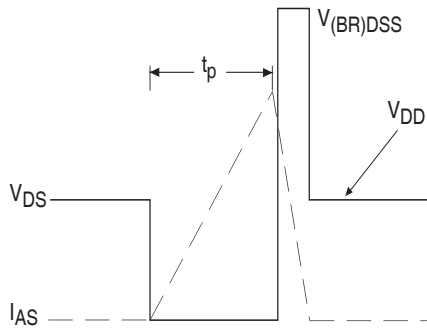


Fig 12b. Unclamped Inductive Waveforms

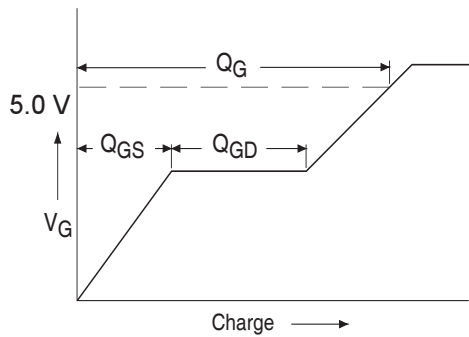


Fig 13a. Basic Gate Charge Waveform

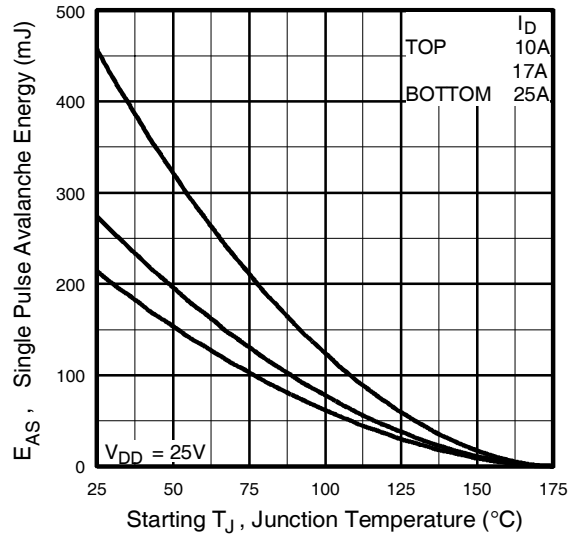


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

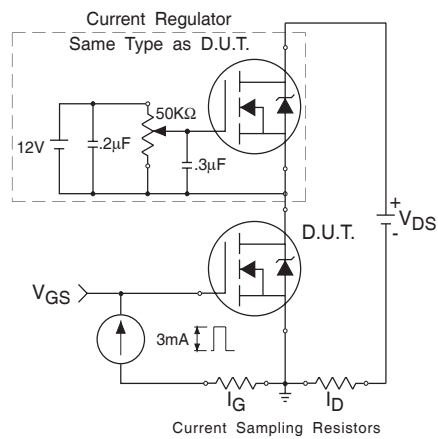
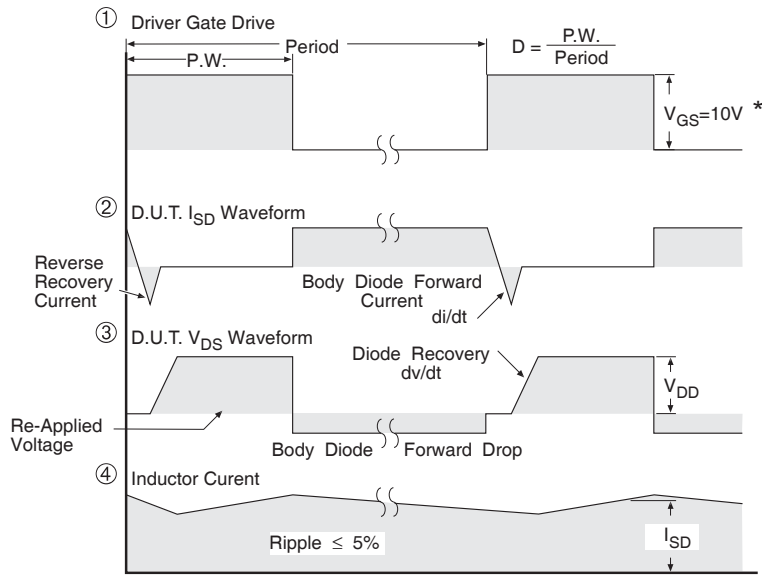
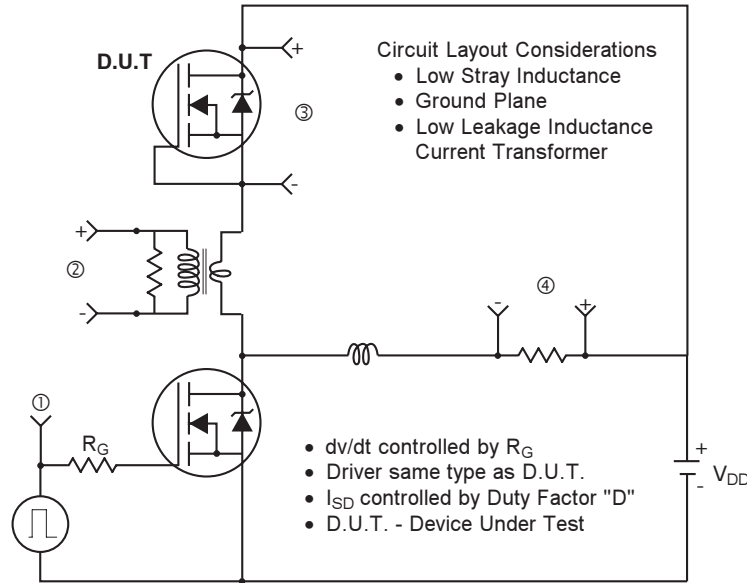


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

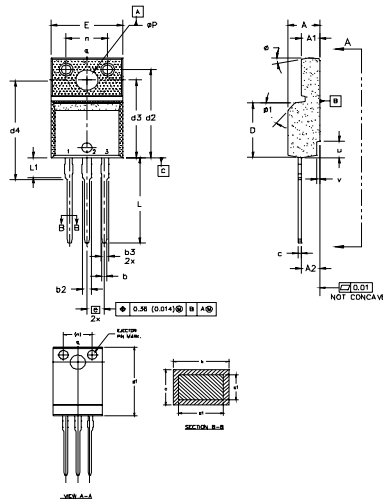
Fig 14. For N-Channel HEXFETS

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TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)

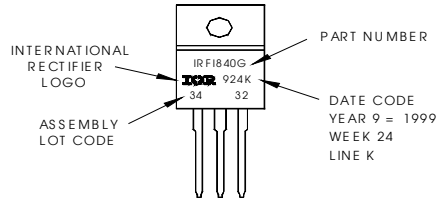


NOTES:
 1.0 DIMENSIONS AND TOLERANCING PER ASME Y14.5 M-1994
 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1
 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.0075 (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OVERMOUNT EXTREMITY OF THE PLASTIC BODY.
 DIMENSIONS IN APPLY TO BRASS METAL ONLY.
 5.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
 7.0 CONTROLLING DIMENSION L, INCHES.

SYMBOL	DIMENSIONS		NOTES	LEAD ASSIGNMENTS
	MILLIMETERS	INCHES		
A	4.57	0.180	0.180	
A1	2.57	0.101	0.114	
A2	2.51	0.099	0.112	
B	0.632	0.024	0.024	5
B1	0.632	0.024	0.024	
B2	1.228	0.048	0.055	
B3	1.229	0.048	0.055	
C	0.440	0.017	0.025	
C1	0.440	0.017	0.025	
D	8.63	0.341	0.396	4
D1	15.80	0.622	0.635	
D2	15.97	0.630	0.580	
D3	12.30	0.484	0.509	
D4	8.64	0.340	0.390	
E	10.36	0.408	0.419	4
e	2.54	0.100		
L	13.20	0.520	0.641	
L1	3.10	0.122	0.138	5
n	6.09	0.238	0.242	
p	3.05	0.120	0.136	
q	2.40	0.094	0.098	6
r	0.40	0.016	0.020	6
s	7	7	7	
t	45	45	45	

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G
 WITH ASSEMBLY
 LOT CODE 3432
 ASSEMBLED ON WW 24 1999
 IN THE ASSEMBLY LINE "K"
Note: "P" in assembly line
 position indicates "Lead-Free"



Data and specifications subject to change without notice.



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